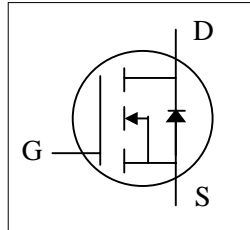




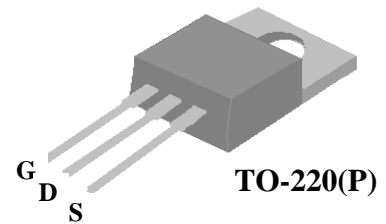
- ▼ Simple Drive Requirement
- ▼ Lower On-resistance
- ▼ Fast Switching Characteristic



BV_{DSS}	60V
$R_{DS(ON)}$	9mΩ
I_D	75A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.



The TO-220 package is widely preferred for commercial-industrial through-hole applications and suited for low voltage applications such as DC/DC converters.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V ³	75	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	57	A
I_{DM}	Pulsed Drain Current ¹	260	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	138	W
	Linear Derating Factor	1.11	W/°C
E_{AS}	Single Pulse Avalanche Energy ⁴	450	mJ
I_{AR}	Avalanche Current	30	A
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	0.9	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	°C/W



AP95T06AGP

Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1mA	60	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =45A	-	-	9	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	4	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =45A	-	39	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =60V, V _{GS} =0V	-	-	10	uA
	Drain-Source Leakage Current (T _j =150°C)	V _{DS} =48V, V _{GS} =0V	-	-	100	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ±20V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =45A	-	53	85	nC
Q _{gs}	Gate-Source Charge	V _{DS} =48V	-	16	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	24	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =30V	-	16	-	ns
t _r	Rise Time	I _D =45A	-	96	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	26	-	ns
t _f	Fall Time	R _D =0.67Ω	-	52	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	2600	4160	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	430	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	270	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =45A, V _{GS} =0V	-	-	1.3	V
t _{rr}	Reverse Recovery Time ²	I _S =20A, V _{GS} =0V	-	46	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	70	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Package limitation current is 75A, calculated continuous current based on maximum allowable junction temperature is 90A.
- 4.Starting T_j=25°C , V_{DD}=30V , L=1mH , R_G=25Ω , I_{AS}=30A.

THIS PRODUCT IS AN ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR CONSUMER MARKET. APPLICATIONS OR USES AS CRITERIAL COMPONENT IN LIFE SUPPORT DEVICE OR SYSTEM ARE NOT AUTHORIZED.

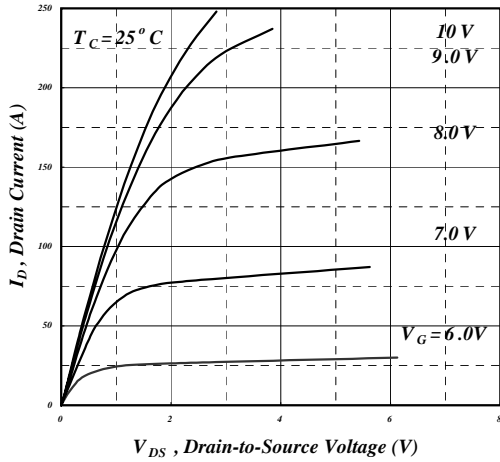


Fig 1. Typical Output Characteristics

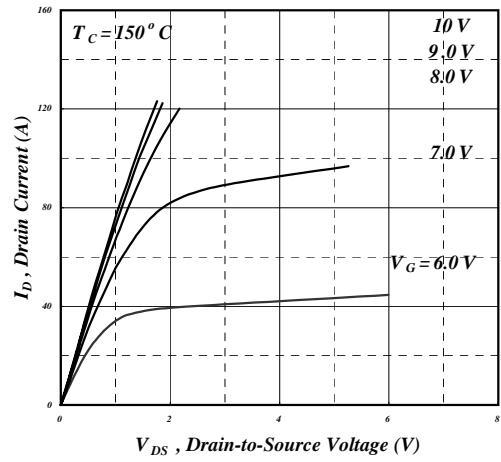


Fig 2. Typical Output Characteristics

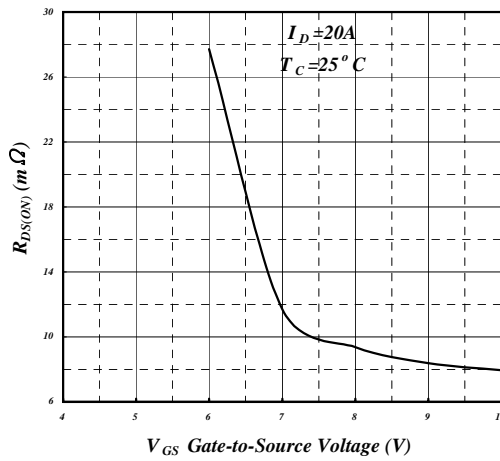


Fig 3. On-Resistance v.s. Gate Voltage

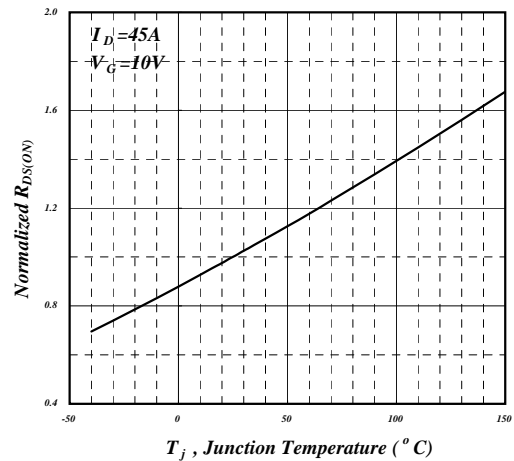


Fig 4. Normalized On-Resistance v.s. Junction Temperature

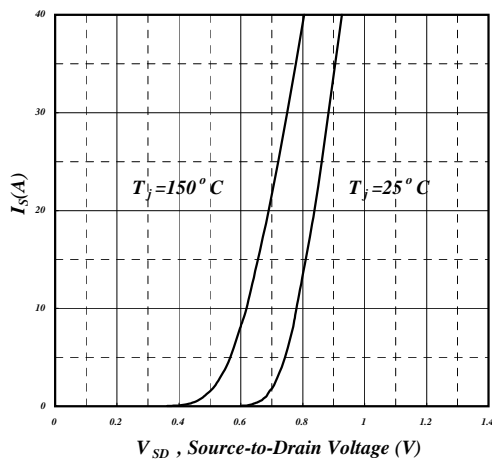


Fig 5. Forward Characteristic of Reverse Diode

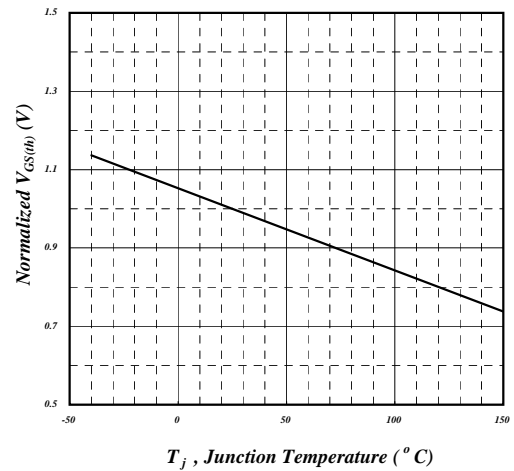


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

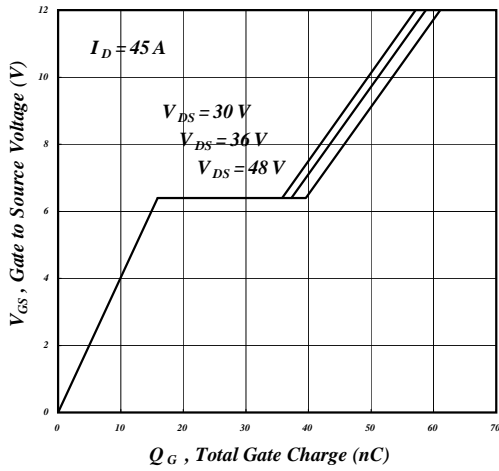


Fig 7. Gate Charge Characteristics

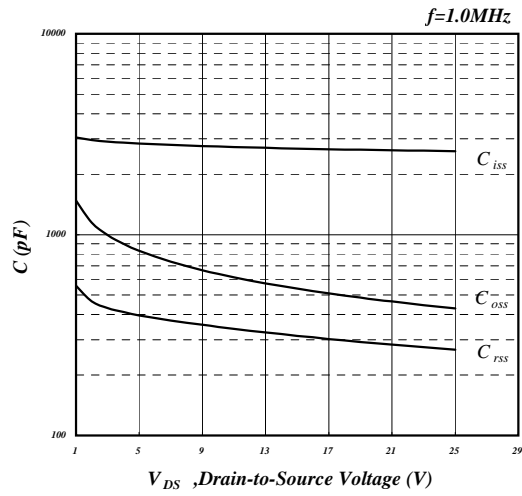


Fig 8. Typical Capacitance Characteristics

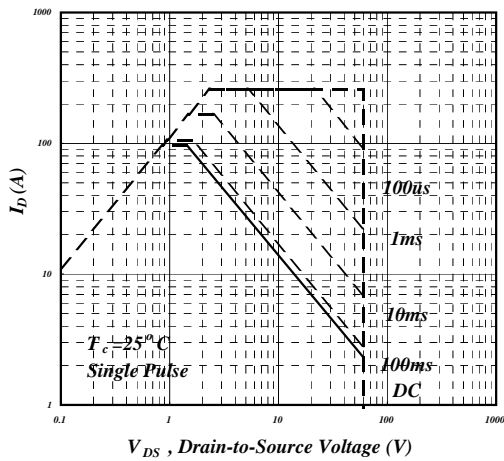


Fig 9. Maximum Safe Operating Area

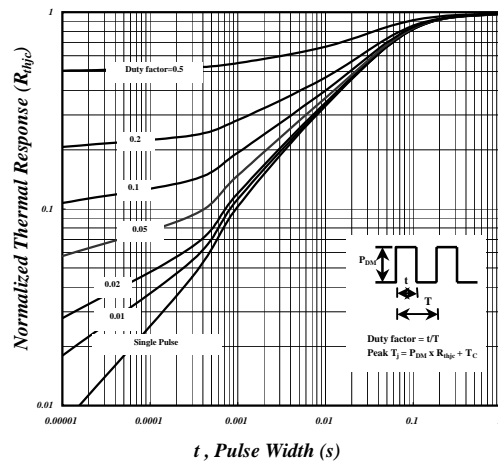


Fig 10. Effective Transient Thermal Impedance

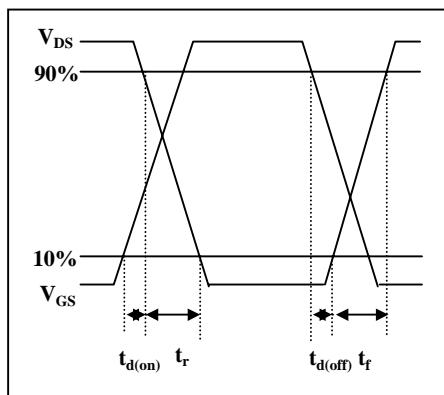


Fig 11. Switching Time Waveform

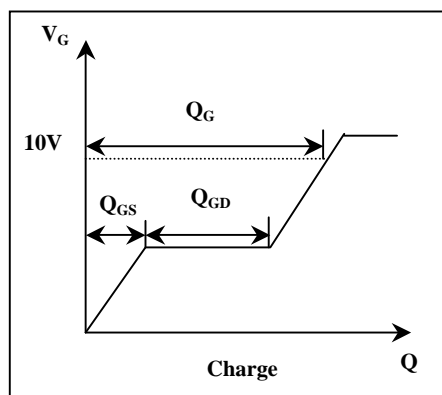
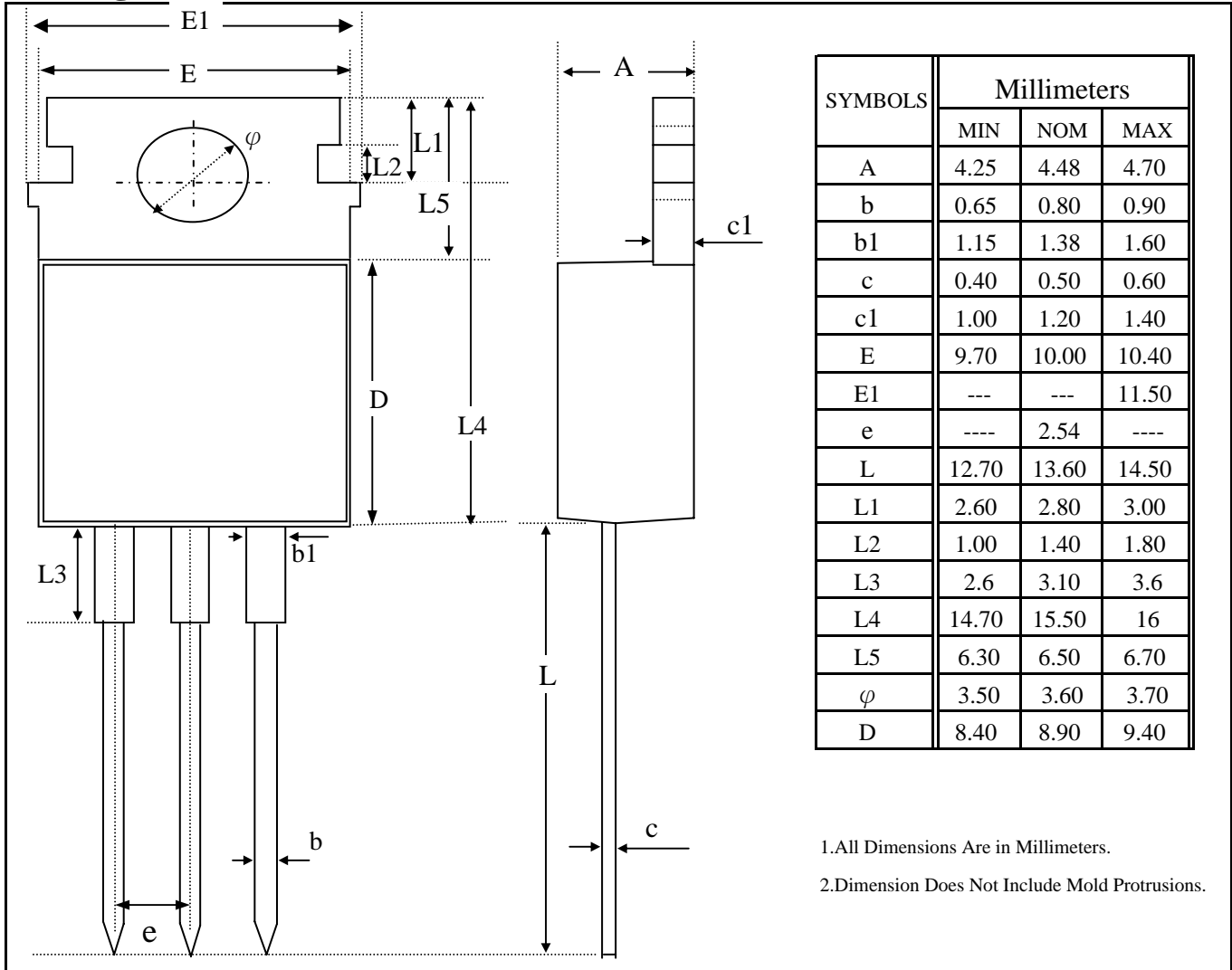


Fig 12. Gate Charge Waveform



Package Outline : TO-220



Part Marking Information & Packing : TO-220

